



Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	4	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	25	mA
				30	
I_H	$I_T=500mA$		MAX.	15	mA
dV/dt	$V_D=670V$ Gate Open $T_j=125$		MIN.	200	V/ μs
(dI/dt)c	(dV/dt)c=10V/ μs $T_j=125$		MIN.	3	A/ms
t_{on}	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	2.5	μs

FIG.1: Maximum power dissipation versus RMS on-state current

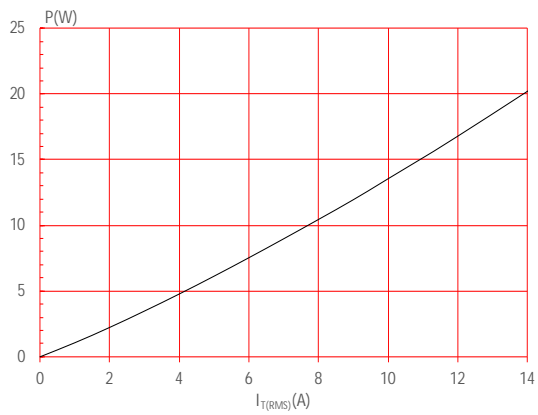


FIG.2: RMS on-state current versus case temperature

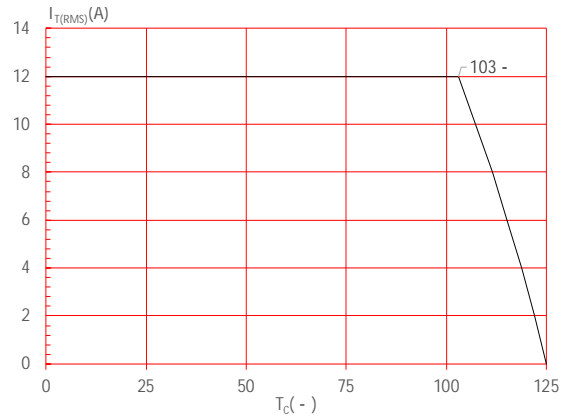


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness:35μm)(full cycle)

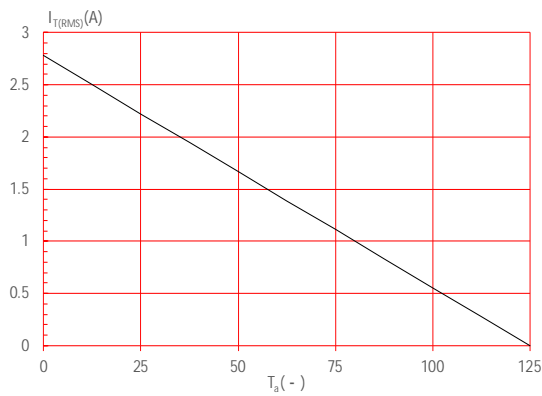


FIG.4: Surge peak on-state current versus number of cycles

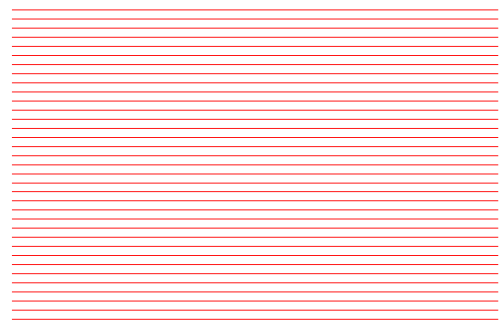
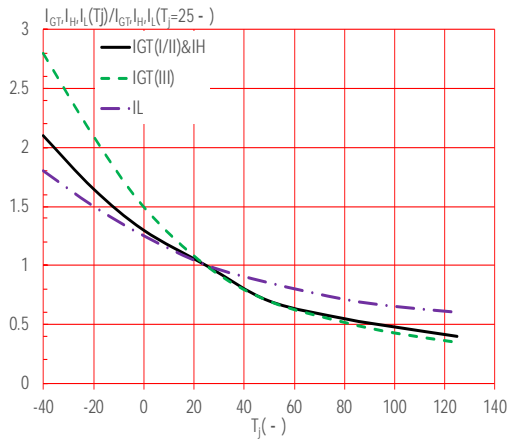
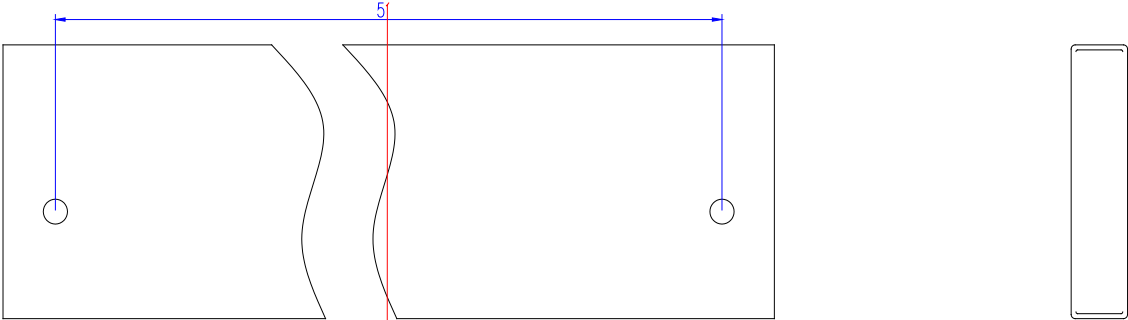


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



DELIVERY MODE



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